

9. (Amended) Data storage system including a magneto-resistive device according to claim 1.

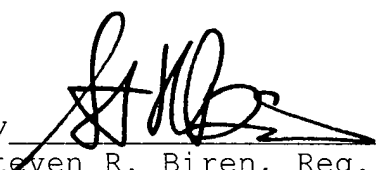
10. (Amended) Magnetic memory including a magneto-resistive device according to claim 1.

REMARKS

The claims have been amended in order to reformat the claims to delete all multiple dependencies prior to calculation of the filing fee and place the instant application in standard U.S. format.

Entry of this amendment prior to calculating the filing fee is respectfully requested.

Respectfully submitted,

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APPENDIX

4. (Amended) Device as claimed in claim 1 ~~or 2~~, in which each of the intermediate layers of the AAF is a Ru layer.

5. (Amended) Device as claimed in claim 1 ~~any of the claims 1 to 4~~, in which the exchange biasing layer is arranged between the substrate and the AAF layer system.

6. (Amended) Device as claimed in claim 1 ~~any of the claims 1 to 5~~, wherein within the odd number of non-adjacent ferromagnetic layers form a stack of layers.

9. (Amended) Data storage system including a magneto-resistive device according to claim 1 ~~any one of the preceding claims 1 to 8~~.

10. (Amended) Magnetic memory including a magneto-resistive device according to claim 1 ~~any one of the preceding claims 1 to 8~~.